

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	27	(boyd-john redeker-fred yezdi-dordi). in.	US-PGPUB; USPAT	OR	OFF	2006/07/21 17:06
S2	955	(lap\$4 grind\$3 abrad\$3 polish\$4 planariz\$6) with (MR magnetorheologic\$4)	US-PGPUB; USPAT	OR	OFF	2006/07/21 17:36
S3	1468	(lap\$4 grind\$3 abrad\$3 polish\$4 planariz\$6) with (electromagnetic\$4)	US-PGPUB; USPAT	OR	OFF	2006/07/21 17:08
S4	2400	S2 S3	US-PGPUB; USPAT	OR	OFF	2006/07/21 17:08
S5	966	S4 AND (WAFER SEMICONDUCTOR)	US-PGPUB; USPAT	OR	OFF	2006/07/21 17:33
S6	25	S5 AND COMPLIANT	US-PGPUB; USPAT	OR	OFF	2006/07/21 17:33
S7	680	(lap\$4 grind\$3 abrad\$3 polish\$4 planariz\$6) with (COMPLIANT)	US-PGPUB; USPAT	OR	OFF	2006/07/21 17:36
S8	104	(lap\$4 grind\$3 abrad\$3 polish\$4 planariz\$6) with (COMPLIANT) WITH (WAFER SEMICONDUCTOR)	US-PGPUB; USPAT	OR	OFF	2006/07/21 17:39
S9	169	("451"/\$ 156/345.14) AND ((COMPLIANT) SAME (WAFER SEMICONDUCTOR))	US-PGPUB; USPAT	OR	OFF	2006/07/21 17:40
S10	13	grind\$3 and subaperture	US-PGPUB; USPAT	OR	OFF	2006/07/24 15:04
S11	49	156/345.14 and (compliant diamond abrasive)	US-PGPUB; USPAT	OR	OFF	2006/07/24 15:12
S12	583	"451"/\$ and (grind\$3 lap\$4 abrad\$3) with (wafer semiconductor) and (diamond compliant)	US-PGPUB; USPAT	OR	OFF	2006/07/24 15:13
S13	168	"451"/\$ and (grind\$3 lap\$4 abrad\$3) with (wafer semiconductor) same(diamond compliant)	US-PGPUB; USPAT	OR	OFF	2006/07/24 15:23
S14	1221	451/56	US-PGPUB; USPAT	OR	OFF	2006/07/24 15:24
S15	1001	451/57	US-PGPUB; USPAT	OR	OFF	2006/07/24 15:24
S16	504	S15 and (wafe semiconductor)	US-PGPUB; USPAT	OR	OFF	2006/07/24 15:24
S17	32362	(electromagnetic) same (grind\$3 condition\$3 dress\$3 roughen\$3)	US-PGPUB; USPAT	OR	OFF	2007/03/15 08:36
S18	2116	(electromagnetic) same (grind\$3 condition\$3 dress\$3 roughen\$3) same (membrane fluid bladder)	US-PGPUB; USPAT	OR	OFF	2007/03/15 08:37

## EAST Search History

S19	113	(magnetorheological) same (grind\$3 condition\$3 dress\$3 roughen\$3) same (membrane fluid bladder)	US-PGPUB; USPAT	OR	OFF	2007/03/15 08:40
S20	2096	S18 not S19	US-PGPUB; USPAT	OR	OFF	2007/03/15 09:53
S21	12	S19 and (wafer\$1 semiconductor\$1)	US-PGPUB; USPAT	OR	OFF	2007/03/15 08:41
S22	32	"6129808"	US-PGPUB; USPAT	OR	OFF	2007/03/15 09:54
S23	1	"200252207"	EPO; JPO; DERWENT	OR	OFF	2007/03/15 09:55
S24	3	"2002252207"	EPO; JPO; DERWENT	OR	OFF	2007/03/15 09:56
S25	3	"2002252209"	EPO; JPO; DERWENT	OR	OFF	2007/03/15 09:57
S26	114	("y.sub.2 adj o.sub.3" or "yttrium oxide") same plasma	EPO; JPO; DERWENT	OR	OFF	2007/03/15 09:58
S27	26	("y.sub.2 adj o.sub.3" or "yttrium oxide") same plasma same spray\$3	EPO; JPO; DERWENT	OR	OFF	2007/03/15 10:01
S28	154	("y.sub.2 adj o.sub.3" or "yttrium oxide") same plasma same spray\$3	US-PGPUB; USPAT	OR	OFF	2007/03/15 10:01
S29	1040	(lap\$4 grind\$3 abrad\$3 polish\$4 planariz\$6) with (MR magnetorheologic\$4)	US-PGPUB; USPAT	OR	OFF	2007/03/15 14:51
S30	1576	(lap\$4 grind\$3 abrad\$3 polish\$4 planariz\$6) with (electromagnetic\$4)	US-PGPUB; USPAT	OR	OFF	2007/03/15 14:51
S31	524	(S29 S30) and abrasive\$1	US-PGPUB; USPAT	OR	OFF	2007/03/15 15:34
S32	15	(electromagnetic magnetorheological) same (abrasive\$1) same (lap\$4 grind\$3 abrad\$3 polish\$3 planariz\$6). CLM,AB,TI.	US-PGPUB; USPAT	OR	OFF	2007/03/15 16:44
S33	937	(electromagnetic magnetorheological) and(abrasive\$1).CLM,AB,TI.	US-PGPUB; USPAT	OR	OFF	2007/03/15 16:45
S34	0	(magnetorheological) and(abrasive\$1). CLM,AB,TI.	US-PGPUB; USPAT	OR	OFF	2007/03/15 16:45
S35	0	(magnetorheological) and(abrasive\$1). CLM,AB,TI.	US-PGPUB; USPAT	OR	OFF	2007/03/15 16:45